

	<p>SIE836DF-T1-GE3</p>
	<p>Hersteller-Teilenummer: SIE836DF-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET N-CH 200V 18.3A POLARPAK</p>
<p>Image may be representation. See specs for product details.</p>	<p>Datenblätter:  SIE836DF-T1-GE3.pdf</p>
	<p>RoHS Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

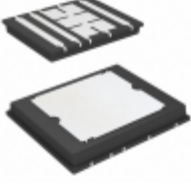
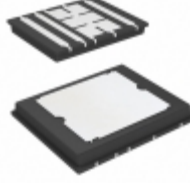
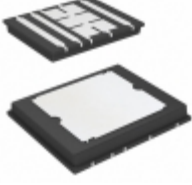
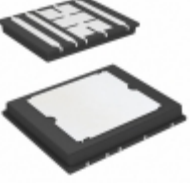
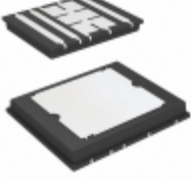
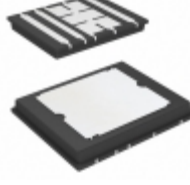
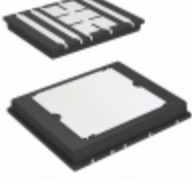
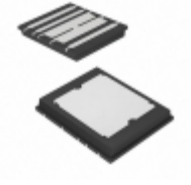
Spezifikationen

Teilenummer	SIE836DF-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 200V 18.3A POLARPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	Require For Quote & Check Stock
VGS (th) (Max) @ Id	4.5V @ 250µA
Vgs (Max)	±30V
Technologie	MOSFET (Metal Oxide)
Supplier Device-Gehäuse	10-PolarPAK® (SH)
Serie	TrenchFET®
Rds On (Max) @ Id, Vgs	130 mOhm @ 4.1A, 10V
Verlustleistung (max)	5.2W (Ta), 104W (Tc)
Verpackung	Tape & Reel (TR)
Verpackung / Gehäuse	10-PolarPAK® (SH)
Andere Namen	SIE836DF-T1-GE3TR
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Eingabekapazität (Ciss) (Max) @ Vds	1200pF @ 100V
Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
Typ FET	N-Channel
FET-Merkmal	-
Antriebsspannung (Max Rds On, Min Rds On)	10V
Drain-Source-Spannung (Vdss)	200V
detaillierte Beschreibung	N-Channel 200V 18.3A (Tc) 5.2W (Ta), 104W (Tc)
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	18.3A (Tc)

SIE836DF-T1-GE3 Electronic Components ist ein 100% neues Original von YIC Distributor, SIE836DF-T1-GE3-Datenblätter durchsuchen, PDF, Inventar bei Y-IC.com Online, SIE836DF-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen bestellen. Versand per DHL / FedEx / TNT / UPS Express. Unterstützung der Zahlung mit telegrafischer Überweisung (T / T) oder PayPal.

RFQ SIE836DF-T1-GE3 E-Mail: Info@Y-IC.com

Sie können auch interessiert

<p>sein:</p>  <p>SIE836DF-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 200V 18.3A POLARPAK</p>	 <p>SIE836DF-T1-E3 Vishay Siliconix MOSFET N-CH 200V 18.3A POLARPAK</p>	 <p>SIE848DF-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A POLARPAK</p>	 <p>SIE844DF-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 44.5A POLARPAK</p>
 <p>SIE844DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 44.5A POLARPAK</p>	 <p>SIE844DF-T1-GE3 Vishay Siliconix MOSFET N-CH 30V 44.5A POLARPAK</p>	 <p>SIE844DF-T1-E3 Vishay Siliconix MOSFET N-CH 30V 44.5A POLARPAK</p>	 <p>SIE836DF-T1-GE3 Vishay Siliconix MOSFET N-CH 200V 18.3A POLARPAK</p>

Verwandtes Hot-Keyword

Mehr

SIE836DF-T1-GE3 Electro-Films (EFI) / Vishay	SIE836DF-T1-GE3 Datenblatt	SIE836DF-T1-GE3-Datenblätter	SIE836DF-T1-GE3 PDF	Electro-Films (EFI) / Vishay SIE836DF-T1-GE3
SIE836DF-T1-GE3 Electronic	SIE836DF-T1-GE3-Komponenten	SIE836DF-T1-GE3-Verteiler	SIE836DF-T1-GE3-Bild	SIE836DF-T1-GE3-Teil
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SIE836DF-T1-GE3 Neu	SIE836DF-T1-GE3 Original	SIE836DF-T1-GE3 garantiert	SIE836DF-T1-GE3 RFQ	SIE836DF-T1-GE3 Online bestellen

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